

**HIGH FREQUENCY HIGH-SIDE AND LOW-SIDE GATE DRIVER IN U-DFN3030-10**
**Description**

The DIODES™ DGD05473FNQ is a high-frequency gate driver capable of driving N-channel MOSFETs. The floating high-side driver is rated up to 50V.

The DGD05473FNQ logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with MCUs. UVLO for high-side and low-side protects a MOSFET with loss of supply. To protect MOSFETs, cross conduction prevention logic prevents the HO and LO outputs from being on at the same time.

Fast and well-matched propagation delays allow a higher switching frequency, enabling a smaller, more compact power switching design, using smaller associated components. An internal bootstrap diode is included to minimize space. The DGD05473FNQ is offered in the U-DFN3030-10 package and operates over an extended -40°C to +125°C temperature range.

**Features**

- 50V Floating High-Side Driver
- Drives Two N-Channel MOSFETs in a Half-Bridge Configuration
- 1.5A Source / 2.5A Sink Output Current Capability
- Internal Bootstrap Diode Included
- Undervoltage Lockout for High-Side and Low-Side Drivers
- Delay Matching Maximum of 5ns
- Propagation Delay Typical of 20ns
- Logic Input (HIN, LIN and EN) 3.3V Capability
- Ultra Low Standby Currents (<1µA)
- Extended Temperature Range: -40°C to +125°C
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DGD05473FNQ is suitable for automotive applications requiring specific change control; this part is AEC-Q100 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

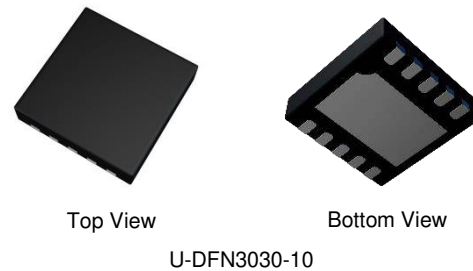
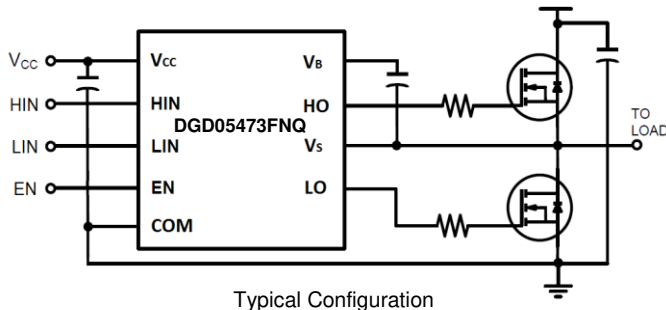
<https://www.diodes.com/quality/product-definitions/>

**Applications**

- DC-DC converters
- Motor controls
- Battery-powered hand tools
- eCig devices
- Class-D power amplifiers

**Mechanical Data**

- Package: U-DFN3030-10
- Package Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—NiPdAu. Solderable per MIL-STD-202, Method 208④
- Weight: 0.017 grams (Approximate)


**Ordering Information** (Note 4)

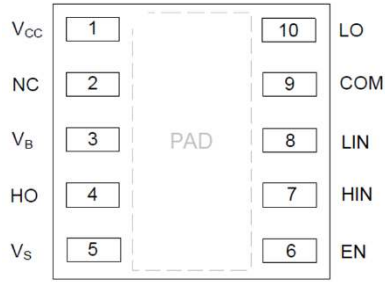
Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DGD05473FNQ-7	DGD05473	7	8	3000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

**Marking Information**


DGD05473 = Product Type Marking Code  
 YY = Year (ex: 22 = 2022)  
 WW = Week (01 to 53)

**Pin Assignments**

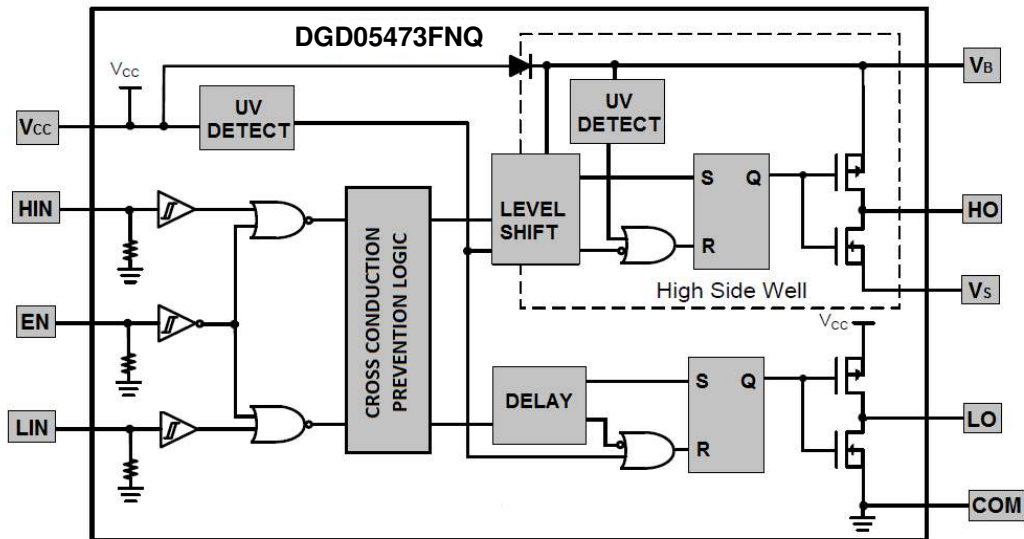


Top View: U-DFN3030-10

**Pin Descriptions**

Pin Number	Pin Name	Function
1	V <sub>CC</sub>	Low-Side and Logic Supply
2	NC	No connection (No Internal Connection)
3	V <sub>B</sub>	High-Side Floating Supply
4	HO	High-Side Gate Drive Output
5	V <sub>S</sub>	High-Side Floating Supply Return
6	EN	Logic Input Enable, a Logic Low turns off Gate Driver
7	HIN	Logic Input for High-Side Gate Driver, in Phase with HO
8	LIN	Logic Input for Low-Side Gate Driver, in Phase with LO
9	COM	Low-Side and Logic Return
10	LO	Low-Side Gate Drive Output
PAD	Substrate	Connect to COM on PCB

**Functional Block Diagram**



**Absolute Maximum Ratings** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Positive Supply Voltage	$V_B$	-0.3 to +60	V
High-Side Floating Negative Supply Voltage	$V_S$	$V_B - 14$ to $V_B + 0.3$	V
High-Side Floating Output Voltage	$V_{HO}$	$V_S - 0.3$ to $V_B + 0.3$	V
Offset Supply Voltage Transient	$dV_S / dt$	50	V/ns
Logic and Low-Side Fixed Supply Voltage	$V_{CC}$	-0.3 to +14	V
Low-Side Output Voltage	$V_{LO}$	-0.3 to $V_{CC} + 0.3$	V
Logic Input Voltage (HIN, LIN and EN)	$V_{IN}$	-0.3 to $V_{CC} + 0.3$	V
Bootstrap Diode Current (Pulsed <math><10\mu\text{s}</math>)	$I_{BD}$	1	A

**Thermal Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	$P_D$	0.4	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	64	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case (Note 5)	$R_{\theta JC}$	42	$^\circ\text{C}/\text{W}$
Operating Temperature	$T_J$	+150	$^\circ\text{C}$
Lead Temperature (Soldering, 10s)	$T_L$	+300	
Storage Temperature Range	$T_{STG}$	-55 to +150	

Note: 5. When mounted on a standard JEDEC 2-layer FR-4 board.

**Recommended Operating Conditions**

Parameter	Symbol	Min	Max	Unit
High-Side Floating Supply	$V_B$	$V_S + 4.4$	$V_S + 14$	V
High-Side Floating Supply Offset Voltage	$V_S$	(Note 6)	50 (Note 7)	V
High-Side Floating Output Voltage	$V_{HO}$	$V_S$	$V_B$	V
Logic and Low Side Fixed Supply Voltage	$V_{CC}$	4.7 (Note 8)	14	V
Low-Side Output Voltage	$V_{LO}$	0	$V_{CC}$	V
Logic Input Voltage (HIN, LIN and EN)	$V_{IN}$	0	5	V
Ambient Temperature	$T_A$	-40	+125	$^\circ\text{C}$

Notes: 6. Logic operation for  $V_S$  of -5V to +50V.

7. Provided  $V_B$  doesn't exceed absolute maximum rating of 60V.

8. For operation of  $V_{CC} = 4.7\text{V}$  to  $4.9\text{V}$ , an external bootstrap Schottky diode (0.3V Vf, 1A) is necessary, see Figure 4. For operation  $V_{CC} \geq 4.9\text{V}$ , the external Schottky diode is not required.

**DC Electrical Characteristics** ( $V_{CC} = V_{BS} = 12V$ ,  $COM = V_S = 0V$ ,  $@T_A = +25^\circ C$ , unless otherwise specified.) (Note 9)

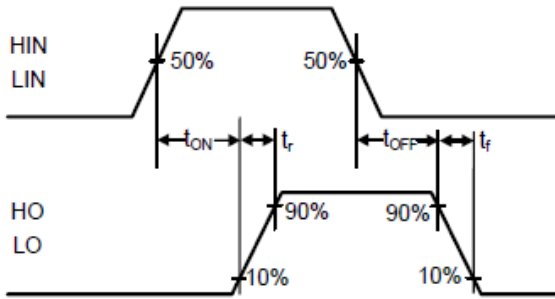
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Logic "1" Input Voltage	$V_{IH}$	2.4	—	—	V	—
Logic "0" Input Voltage	$V_{IL}$	—	—	0.8	V	—
Enable Logic "1" Input Voltage	$V_{ENIH}$	1.6	—	—	V	—
Enable Logic "0" Input Voltage	$V_{ENIL}$	—	—	0.7	V	—
Input Voltage Hysteresis	$V_{INHYS}$	—	0.6	—	V	—
Enable Input Voltage Hysteresis	$V_{ENINHYS}$	—	0.1	—	V	—
High Level Output Voltage, $V_{BIAS} - V_O$	$V_{OH}$	—	0.45	0.6	V	$I_{O+} = 100mA$
Low Level Output Voltage, $V_O$	$V_{OL}$	—	0.15	0.22	V	$I_{O-} = 100mA$
Offset Supply Leakage Current	$I_{LK}$	—	1	5	$\mu A$	$V_B = V_S = 60V$
$V_{CC}$ Shutdown Supply Current	$I_{CCSD}$	—	0	1	$\mu A$	$V_{IN} = 0V$ or $5V$ , $V_{EN} = 0V$
$V_{CC}$ Quiescent Supply Current	$I_{CCQ}$	—	130	200	$\mu A$	$V_{IN} = 0V$ or $5V$
$V_{CC}$ Operating Supply Current	$I_{CCOP}$	—	7.3	—	mA	$f_s = 500kHz$ , $C_L = 1000pF$
$V_{BS}$ Quiescent Supply Current	$I_{BSQ}$	—	40	100	$\mu A$	$V_{IN} = 0V$ or $5V$
$V_{BS}$ Operating Supply Current	$I_{BSOP}$	—	7.3	—	mA	$f_s = 500kHz$ , $C_L = 1000pF$
Logic "1" Input Bias Current	$I_{IN+}$	—	—	50	$\mu A$	$V_{IN} = 5V$
Logic "0" Input Bias Current	$I_{IN-}$	—	—	5	$\mu A$	$V_{IN} = 0V$
Enable Logic "1" Input Bias Current	$I_{ENIN+}$	—	43	60	$\mu A$	$V_{IN} = 5V$
Enable Logic "0" Input Bias Current	$I_{ENIN-}$	—	0	5	$\mu A$	$V_{IN} = 0V$
$V_{BS}$ Supply Undervoltage Positive Going Threshold	$V_{BSUV+}$	3.3	3.8	4.4	V	—
$V_{BS}$ Supply Undervoltage Negative Going Threshold	$V_{BSUV-}$	2.9	3.3	3.9	V	—
$V_{CC}$ Supply Undervoltage Positive Going Threshold	$V_{CCUV+}$	3.3	3.8	4.4	V	—
$V_{CC}$ Supply Undervoltage Negative Going Threshold	$V_{CCUV-}$	2.9	3.3	3.9	V	—
Output High Short Circuit Pulsed Current	$I_{O+}$	1.0	1.5	—	A	$V_O = 0V$ , $PW \leq 10\mu s$
Output Low Short Circuit Pulsed Current	$I_{O-}$	1.9	2.5	—	A	$V_O = 15V$ , $PW \leq 10\mu s$
Forward Voltage of Bootstrap Diode	$V_{F1}$	—	0.67	—	V	$I_F = 100\mu A$
Forward Voltage of Bootstrap Diode	$V_{F2}$	—	1.2	—	V	$I_F = 100mA$

Note: 9. The  $V_{IN}$  and  $I_{IN}$  parameters are applicable to the logic pins: HIN, LIN and EN. The  $V_O$  and  $I_O$  parameters are applicable to the respective output pins: HO and LO.

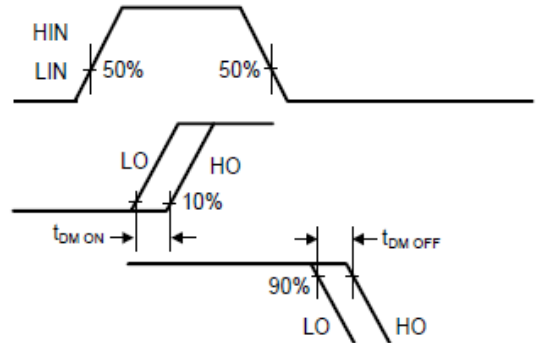
**AC Electrical Characteristics** ( $V_{CC} = V_{BS} = 12V$ ,  $COM = V_S = 0V$ ,  $C_L = 1000pF$ ,  $@T_A = +25^\circ C$ , unless otherwise specified.)

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Turn-On Propagation Delay	$t_{ON}$	—	20	35	ns	—
Turn-Off Propagation Delay	$t_{OFF}$	—	23	56	ns	$V_S = 50V$
Delay Matching, HO & LO Turn-On	$t_{DM}$	—	—	5	ns	—
Turn-On Rise Time	$t_r$	—	16	30	ns	—
Turn-Off Fall Time	$t_f$	—	12	25	ns	—

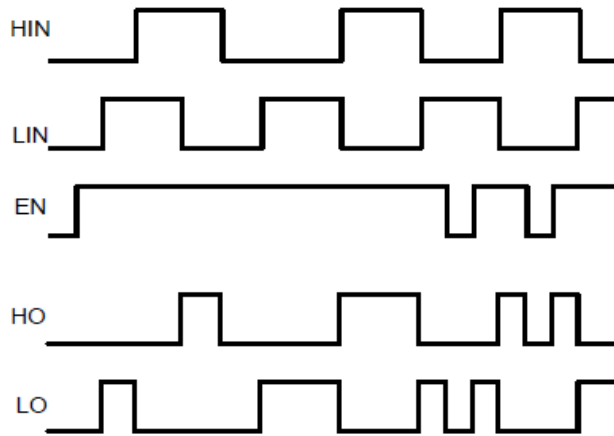
**Timing Waveforms**



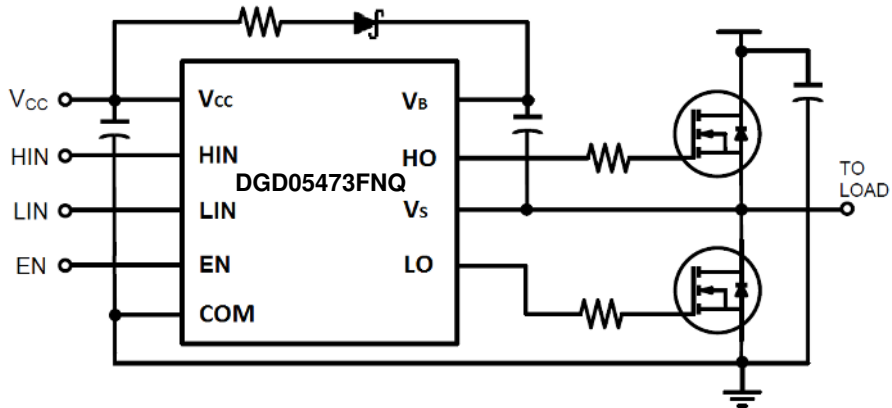
**Figure 1. Switching Time Waveform Definitions**



**Figure 2. Delay Matching Waveform Definitions**



**Figure 3. Input / Output Timing Diagram**



**Figure 4. Typical application necessary for  $V_{CC} = 4.7V$  to  $4.9V$  operation. For  $V_{CC} \geq 4.9V$ , the bootstrap Schottky diode (0.3V Voltage drop, 1A) and resistor are not required.**

**Typical Performance Characteristics** ( $V_{CC} = 12V$ ,  $@T_A = +25^\circ C$ , unless otherwise specified.)

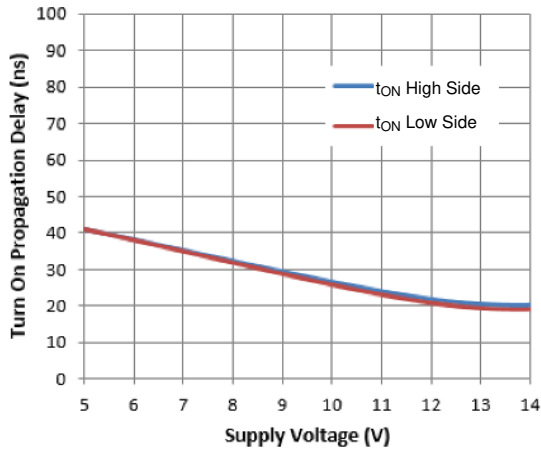


Figure 5. Turn-on Propagation Delay vs. Supply Voltage

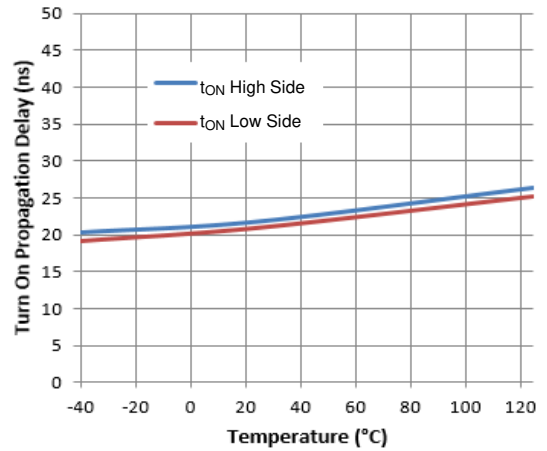


Figure 6. Turn-on Propagation Delay vs. Temperature

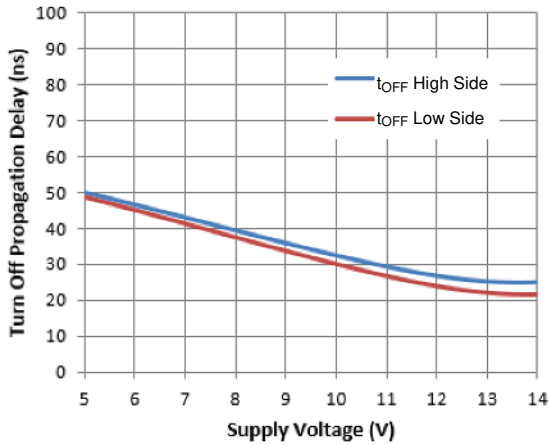


Figure 7. Turn-off Propagation Delay vs. Supply Voltage

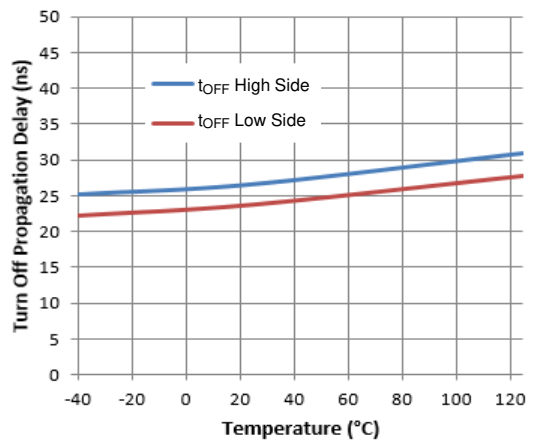


Figure 8. Turn-off Propagation Delay vs. Temperature

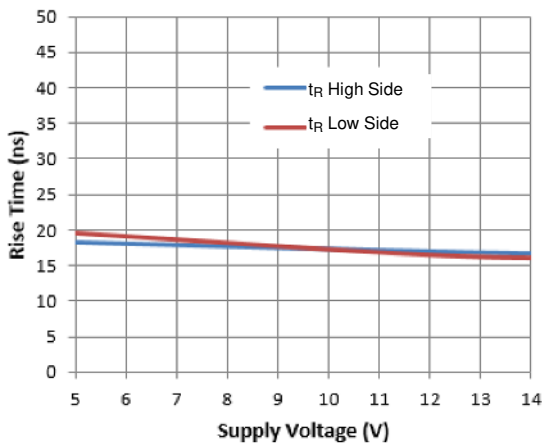


Figure 9. Rise Time vs. Supply Voltage

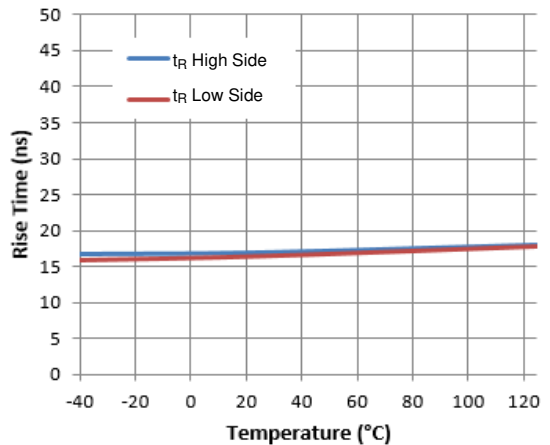


Figure 10. Rise Time vs. Temperature

**Typical Performance Characteristics** (continued)

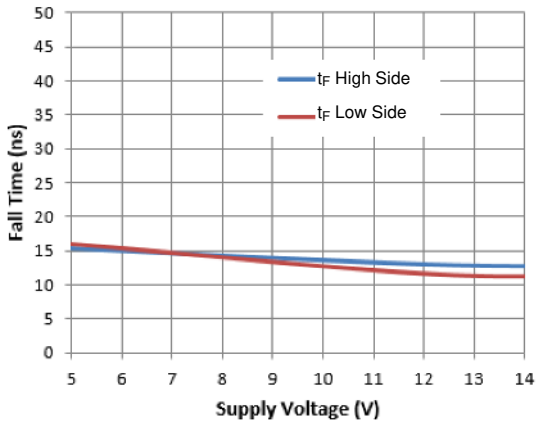


Figure 11. Fall Time vs. Supply Voltage

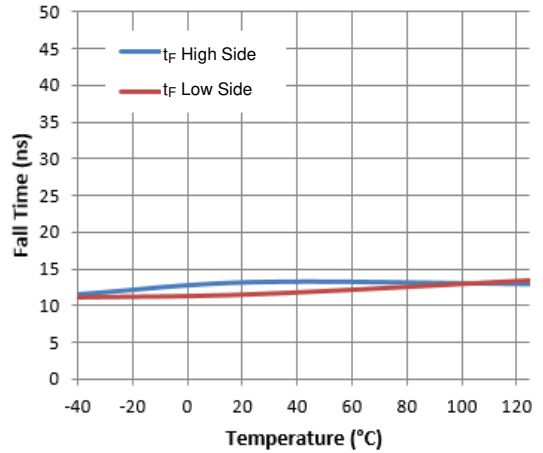


Figure 12. Fall Time vs. Temperature

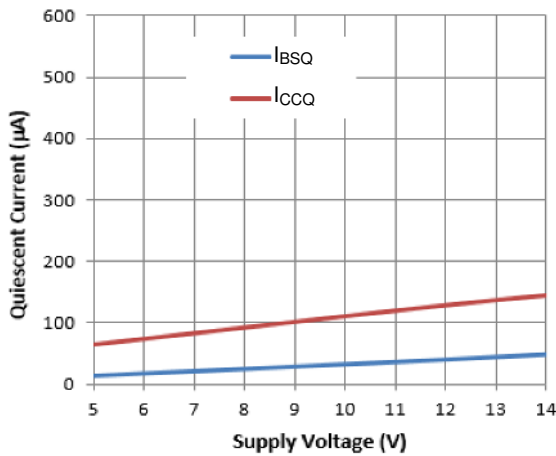


Figure 13. Quiescent Current vs. Supply Voltage

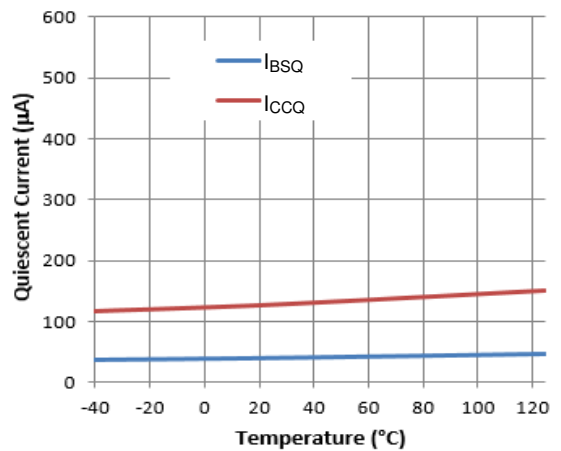


Figure 14. Quiescent Current vs. Temperature

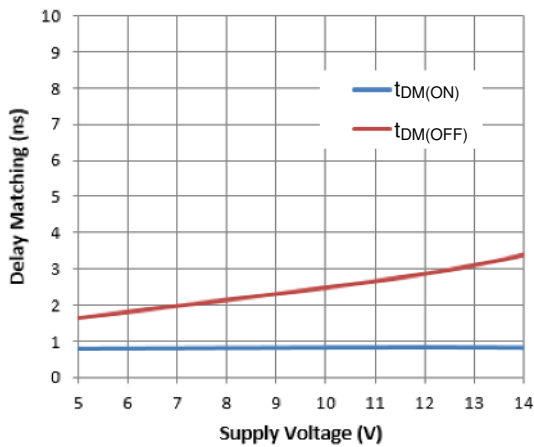


Figure 15. Delay Matching vs. Supply Voltage

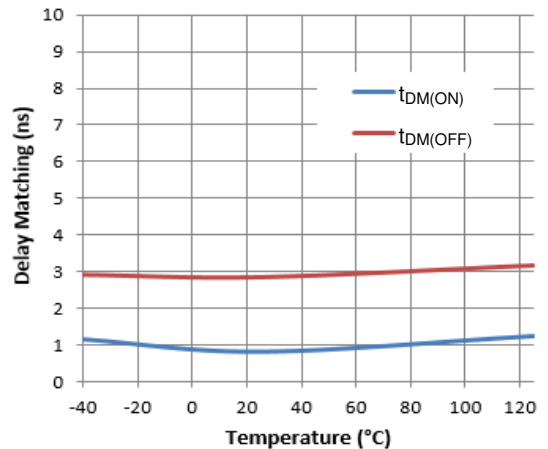


Figure 16. Delay Matching vs. Temperature

**Typical Performance Characteristics** (continued)

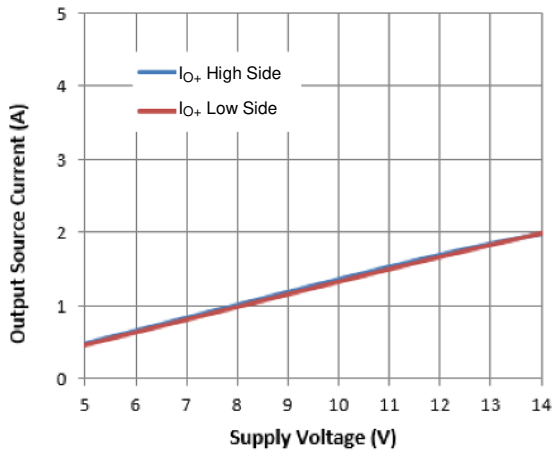


Figure 17. Output Source Current vs. Supply Voltage

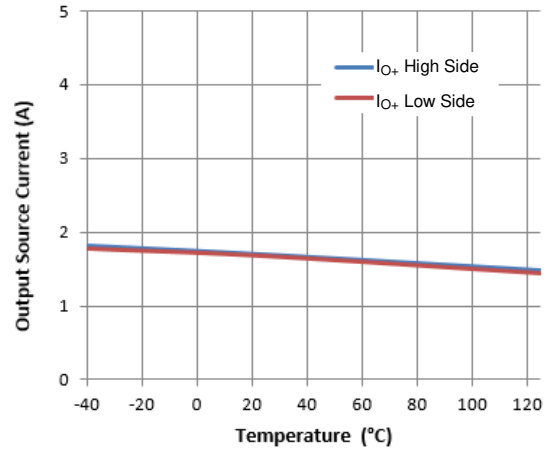


Figure 18. Output Source Current vs. Temperature

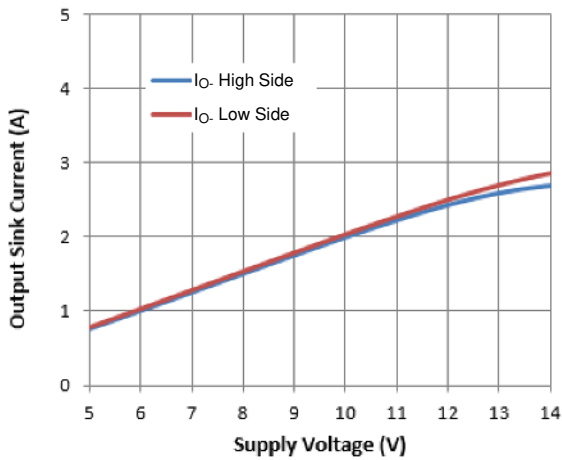


Figure 19. Output Sink Current vs. Supply Voltage

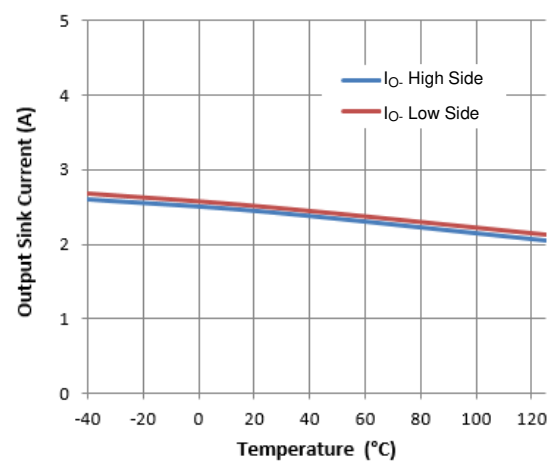


Figure 20. Output Sink Current vs. Temperature

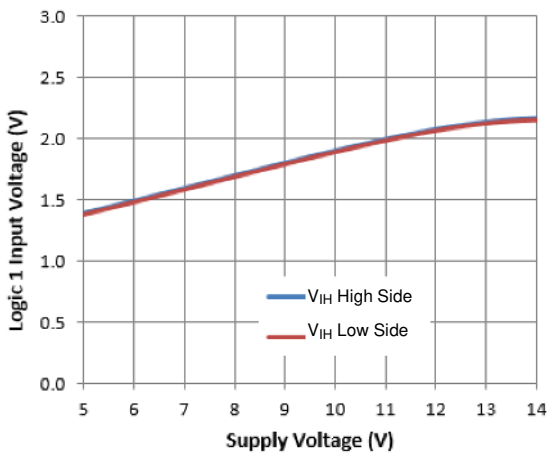


Figure 21. Logic 1 Input Voltage vs. Supply Voltage

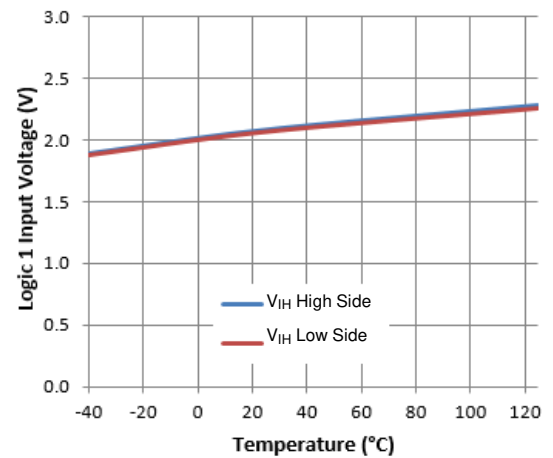


Figure 22. Logic 1 Input Voltage vs. Temperature



**Typical Performance Characteristics** (continued)

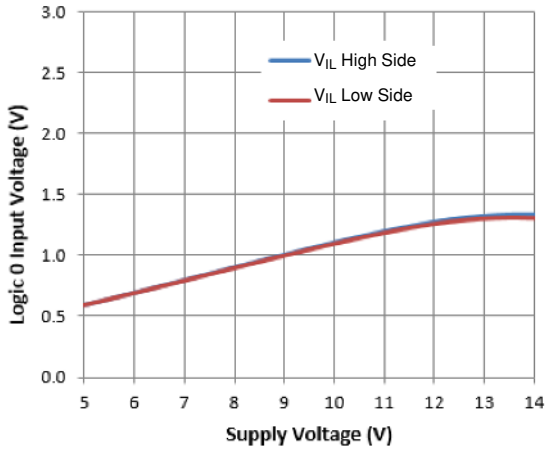


Figure 23. Logic 0 Input Voltage vs. Supply Voltage

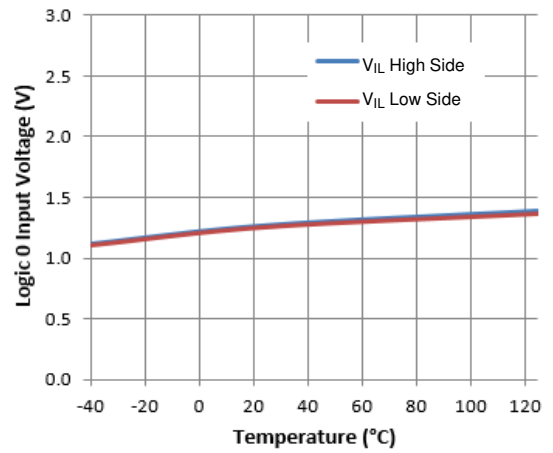


Figure 24. Logic 0 Input Voltage vs. Temperature

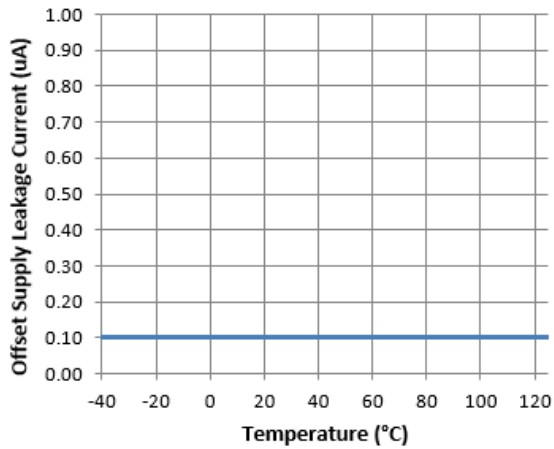
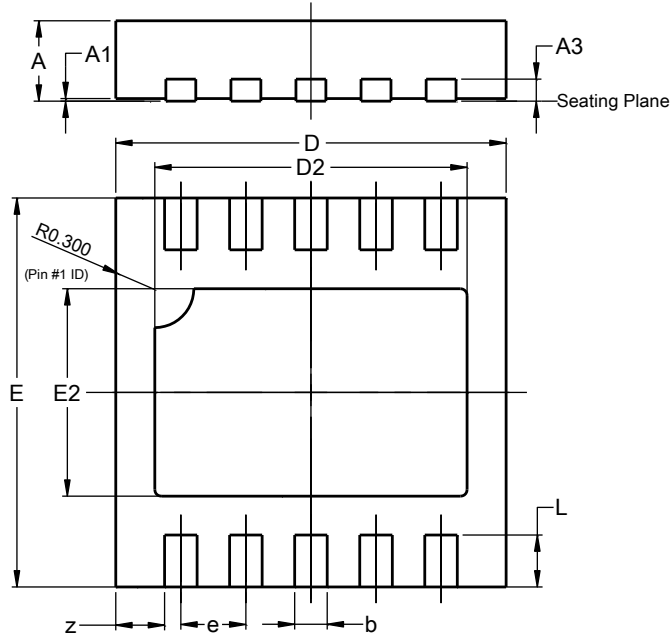


Figure 25. Offset Supply Leakage Current vs. Temperature

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### U-DFN3030-10

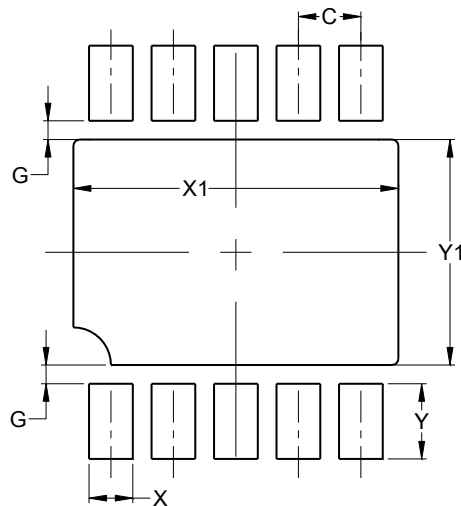


U-DFN3030-10			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0.00	0.05	0.02
A3	--	--	0.15
b	0.20	0.30	0.25
D	2.90	3.10	3.00
D2	2.30	2.50	2.40
E	2.90	3.10	3.00
E2	1.50	1.70	1.60
e	--	--	0.50
L	0.25	0.55	0.40
z	--	--	0.375
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### U-DFN3030-10



Dimensions	Value (in mm)
C	0.50
G	0.15
X	0.35
X1	2.60
Y	0.60
Y1	1.80

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